

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)

2. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

a polymer compound produced by addition polymerization having an epoxy group;

a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl groups; and

~~a solvent;~~ a solvent; and

a light absorbing compound.

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

3. (Previously Presented) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

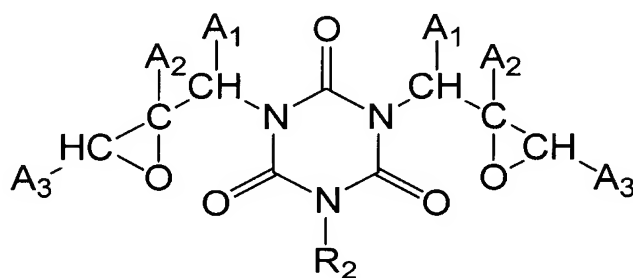
an s-triazine trione skeleton compound with a molecular weight of 2000 or less having at least two epoxy groups;

a polymer compound having a phenolic hydroxyl group, a carboxyl group, a protected carboxyl group or an acid anhydride structure; and

a solvent,

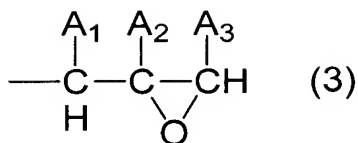
wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

4. (Canceled)
5. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a carboxyl group is a compound having acrylic acid or methacrylic acid as a unit structure.
6. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a phenolic hydroxyl group is a compound having hydroxystyrene as a unit structure.
7. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound having at least three epoxy groups and no aromatic ring structure.
8. (Canceled)
9. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound of formula (2)



(2)

wherein A₁, A₂ and A₃ each are hydrogen atom, methyl group or ethyl group, R₂ is hydrogen atom, C₁₋₆ alkyl group, C₃₋₆ alkenyl group, benzyl group, phenyl group or a group of formula (3)



10-12. (Canceled)

13. (Currently Amended) A method for forming photoresist ~~pattern~~ patterns for use in manufacture of semiconductor ~~device~~ devices, comprising

coating ~~the~~ an underlayer forming composition ~~according to claim 2~~ on a semiconductor substrate, and baking it to form an underlayer coating,

forming a photoresist layer on the underlayer coating,

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light, and

developing the photoresist layer after the exposure to ~~light~~ light, wherein the underlayer forming composition comprises:

a polymer compound produced by addition polymerization having an epoxy group;

a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl groups; and

a solvent,

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

14. (Original) The method for forming photoresist pattern according to claim 13, wherein the exposure to light is carried out with a light of a wavelength of 248 nm, 193 nm or 157 nm.